

60 V, 1 A PNP/PNP low VCEsat (BISS) transistor

23 January 2013

Product data sheet

1. General description

PNP/PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package.

NPN/PNP complement: PBSS4160PANP. NPN/NPN complement: PBSS4160PAN.

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability ${\sf I}_{\sf C}$ and ${\sf I}_{\sf CM}$
- High collector current gain h_{FE} at high I_C
- Reduced Printed-Circuit Board (PCB) requirements
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Load switch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor								
V _{CEO}	collector-emitter voltage	open base		-	-	-60	V	
I _C	collector current			-	-	-1	А	
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-1.5	А	
Per transistor								
R _{CEsat}	collector-emitter saturation resistance	I _C = -0.5 A; I _B = -50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C		-	-	360	mΩ	

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	6 5 4	C1 B2 E2
2	B1	base TR1		
3	C2	collector TR2	7 8	
4	E2	emitter TR2		
5	B2	base TR2		E1 B1 C2
6	C1	collector TR1	Transparent top view DFN2020-6 (SOT1118)	sym138
7	C1	collector TR1	2	
8	C2	collector TR2		

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PBSS5160PAP	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body $2 \times 2 \times 0.65$ mm	SOT1118				

7. Marking

1	able 4. Marking codes	
•	Type number	Marking code
	PBSS5160PAP	2L

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit			
Per transistor									
V _{CBO}	collector-base voltage	open emitter		-	-60	V			
V _{CEO}	collector-emitter voltage	open base		-	-60	V			
V _{EBO}	emitter-base voltage	open collector		-	-7	V			
I _C	collector current			-	-1	А			
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	-1.5	А			
I _B	base current			-	-0.3	А			
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Symbol	Parameter	Conditions	Mir	n Max	Unit
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms	-	-1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	370	mW
			[2] -	570	mW
			[3] -	530	mW
			[4] -	700	mW
			[5] -	450	mW
			[6] -	760	mW
			[7] -	700	mW
			[8] -	1450	mW
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	510	mW
			[2] -	780	mW
			[3] -	730	mW
			[4] -	960	mW
			[5] -	620	mW
			[6] -	1040	mW
			[Z] -	960	mW
			[8] -	2000	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	5 150	°C
T _{stg}	storage temperature		-65	5 150	°C

Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated and standard footprint.
 Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.

[4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

[5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.

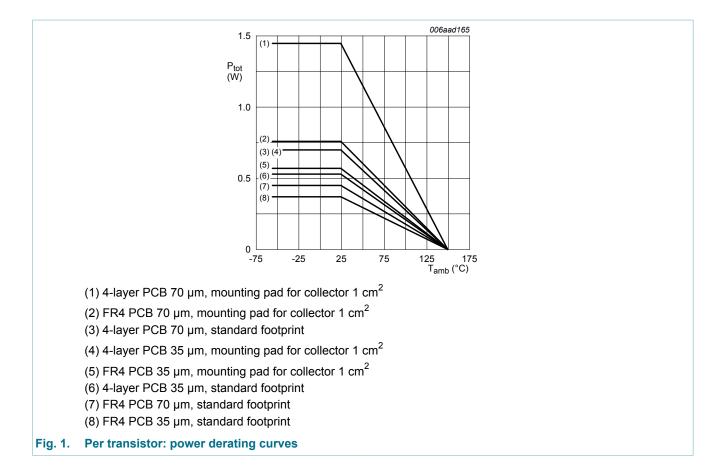
[6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm².

[7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.

[8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

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9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
-		Conditions			176	Шал	
Per transis	tor						
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	338	K/W
	from junction to ambient		[2]	-	-	219	K/W
	ampient		[3]	-	-	236	K/W
			[4]	-	-	179	K/W
			[5]	-	-	278	K/W
			[6]	-	-	164	K/W
			[7]	-	-	179	K/W
			[8]	-	-	86	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	30	K/W

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per device							
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	245	K/W
	from junction to ambient		[2]	-	-	160	K/W
	andient		[3]	-	-	171	K/W
			[4]	-	-	130	K/W
			[5]	-	-	202	K/W
			[6]	-	-	120	K/W
			[7]	-	-	130	K/W
			[8]	-	-	63	K/W

Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated and standard footprint.
 Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.

^[4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

[5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.

[6] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

[7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.

[8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

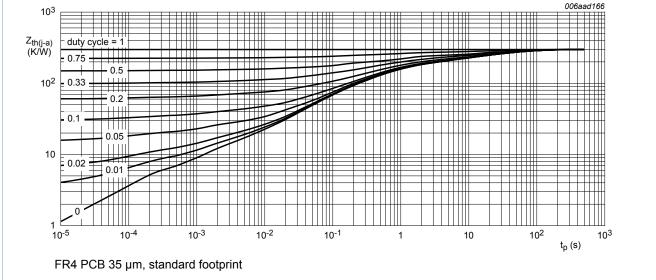
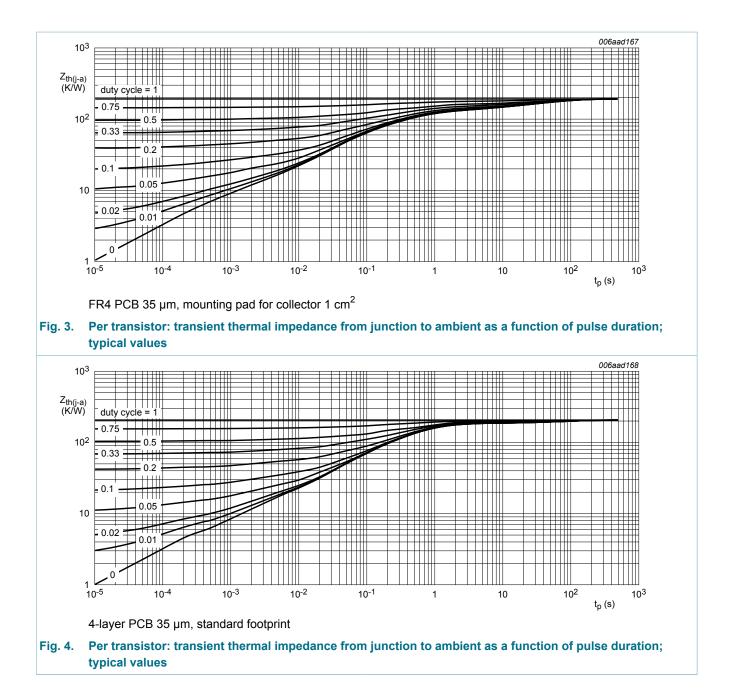


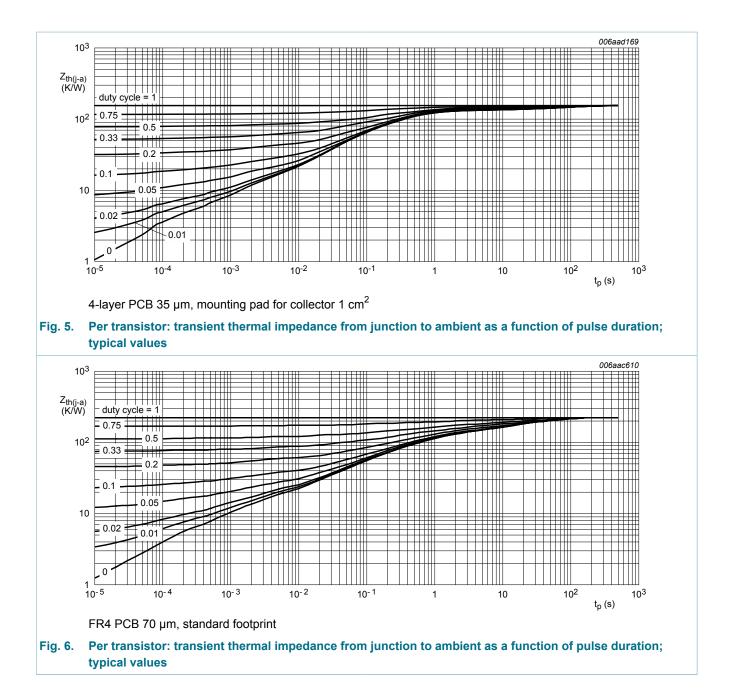
Fig. 2. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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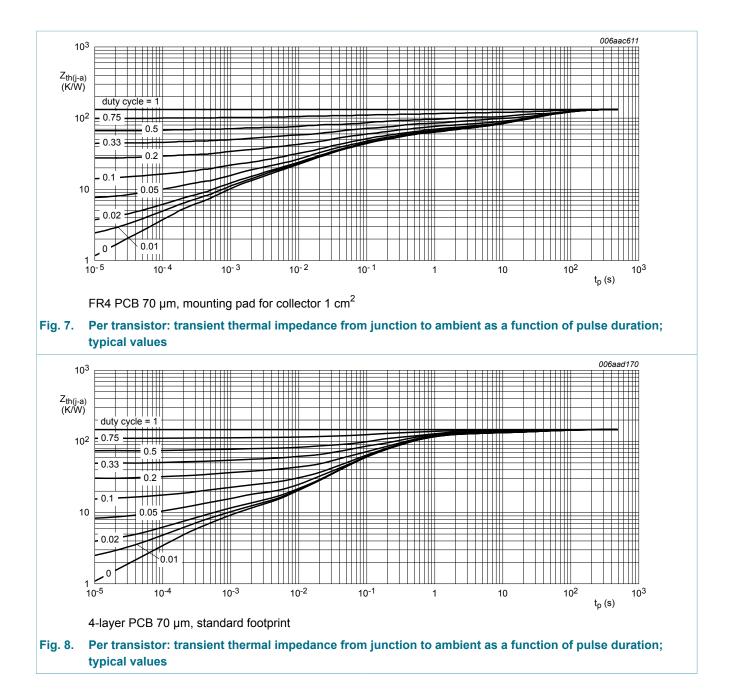






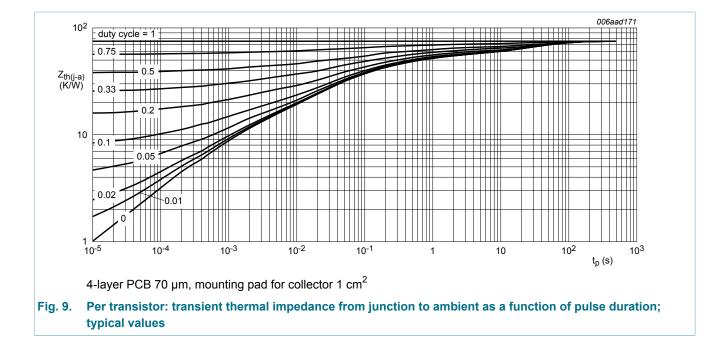






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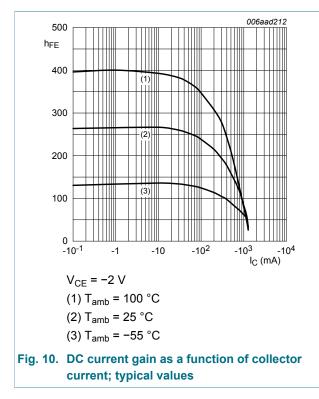
10. Characteristics

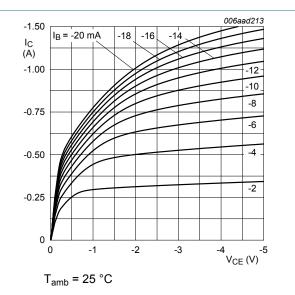
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
I _{CBO}	collector-base cut-off	V _{CB} = -48 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V_{CB} = -48 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	V_{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -2 \text{ V; } I_C = -100 \text{ mA; pulsed;}$ $t_p \le 300 \mu\text{s; } \delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	170	245	-	
		V_{CE} = -2 V; I _C = -500 mA; pulsed; t _p ≤ 300 µs; δ ≤ 0.02 ; T _{amb} = 25 °C	120	170	-	
		$\label{eq:VCE} \begin{array}{l} V_{CE} \texttt{=} \texttt{-2} \; V; \; I_{C} \texttt{=} \texttt{-1} \; A; \; pulsed; \\ t_{p} \texttt{\leq} \texttt{300} \; \mu \texttt{s}; \; \eth \texttt{\leq} \texttt{0.02} \; ; \; T_{amb} \texttt{=} \texttt{25} \; ^{\circ} C \end{array}$	70	100	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -500 mA; I _B = -50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-125	-180	mV
		I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-390	-550	mV
		I_{C} = -1 A; I_{B} = -100 mA; pulsed; t_{p} ≤ 300 µs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-240	-340	mV
R _{CEsat}	collector-emitter saturation resistance	$\begin{split} I_{C} &= -0.5 \text{ A}; \ I_{B} = -50 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300 \mu\text{s}; \ \overline{\delta} &\leq 0.02 ; \ T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-	360	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{BEsat}	base-emitter saturation voltage	I_C = -500 mA; I_B = -50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	-1	V
		I _C = -1 A; I _B = -50 mA; T _{amb} = 25 °C	-	-	-1	V
		I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	-1.1	V
V _{BEon}	base-emitter turn-on voltage	$\label{eq:VCE} \begin{array}{l} V_{CE} = \text{-2 V; } I_{C} = \text{-0.5 A; pulsed;} \\ t_{p} \leq 300 \; \mu s; \; \delta \leq 0.02 \; ; \; T_{amb} = 25 \; ^{\circ}C \end{array}$	-	-	-0.9	V
t _d	delay time	V _{CC} = -10 V; I _C = -0.5 A; I _{Bon} = -25 mA;	-	15	-	ns
t _r	rise time	I _{Boff} = 25 mA; T _{amb} = 25 °C	-	40	-	ns
t _{on}	turn-on time		-	55	-	ns
ts	storage time		-	95	-	ns
t _f	fall time		-	40	-	ns
t _{off}	turn-off time		-	135	-	ns
f _T	transition frequency	V_{CE} = -10 V; I _C = -50 mA; f = 100 MHz; T _{amb} = 25 °C	65	125	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	9.5	13	pF

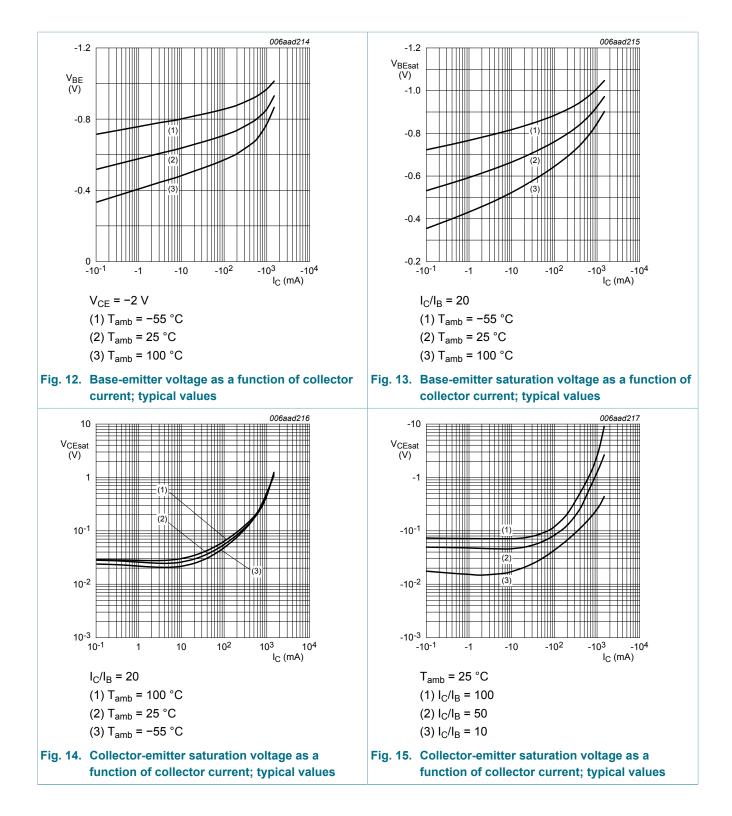








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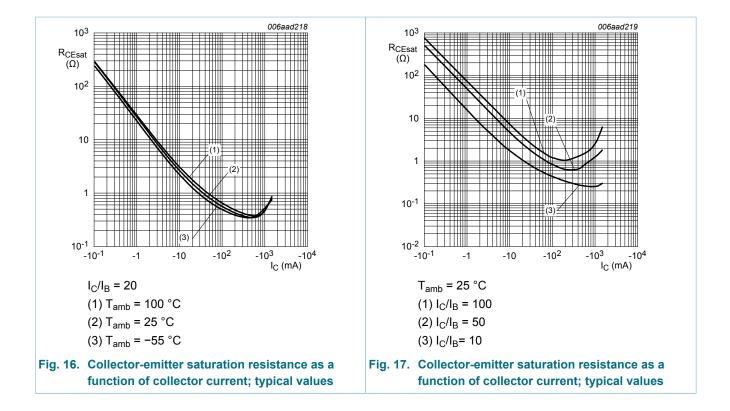


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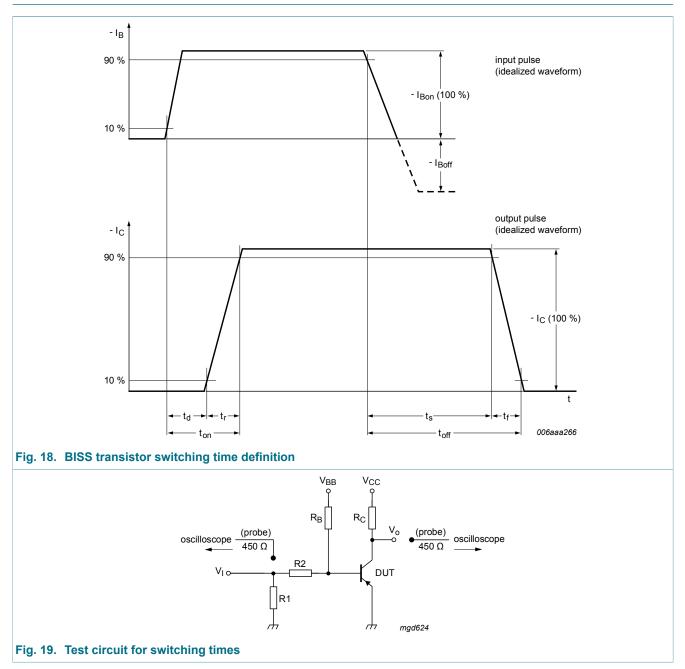
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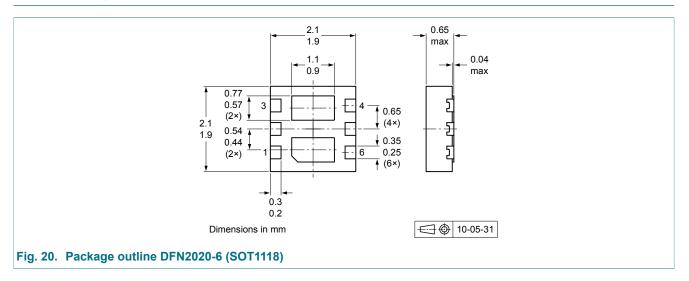
11. Test information



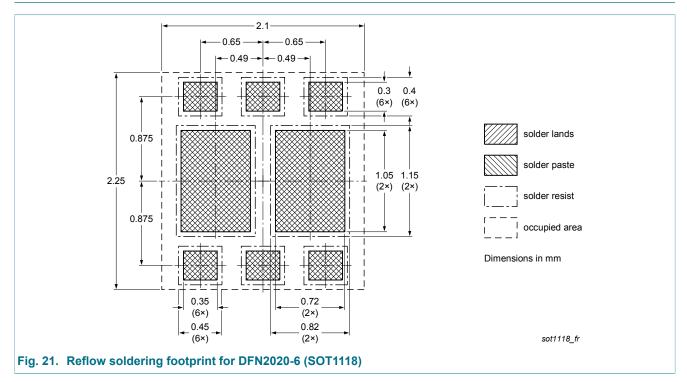
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline



13. Soldering



14. Revision history

Table 8. Revision history								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBSS5160PAP v.1	20130123	Product data sheet	-	-				
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Product data sheet		23 January 2013		14 / 17				

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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